

**• General Description**

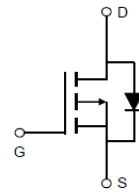
It combines advanced trench MOSFET technology with a low resistance package to provide extremely low  $R_{DS(ON)}$ .

**• Features**

- Advance high cell density Trench technology
- Low  $R_{DS(ON)}$  to minimize conductive loss
- Low Gate Charge for fast switching
- Low Thermal resistance

**• Application**

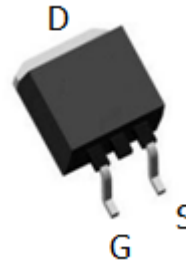
- MB/VGA Vcore
- SMPS 2<sup>nd</sup> Synchronous Rectifier
- POL application
- BLDC Motor driver

**• Product Summary**


$V_{DS} = -30V$

$R_{DS(ON)} = 3.5m\Omega$

$I_D = -120A$


**• Ordering Information:**

Part NO.	ZM035P03B
Marking	ZM035P03
Packing Information	REEL TAPE
Basic ordering unit (pcs)	800

**• Absolute Maximum Ratings ( $T_C = 25^\circ C$ )**

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	$V_{DS}$	-30	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current	$I_D @ TC=25^\circ C$	-120	A
	$I_D @ TC=75^\circ C$	-91	A
	$I_D @ TC=100^\circ C$	-75	A
Pulsed Drain Current	$I_{DM}$	-360	A
Total Power Dissipation( $TC=25^\circ C$ )	$P_D @ TC=25^\circ C$	125	W
Total Power Dissipation( $TA=25^\circ C$ )	$P_D @ TA=25^\circ C$	5	W
Operating Junction Temperature	$T_J$	-55 to 150	$^\circ C$
Storage Temperature	$T_{STG}$	-55 to 150	$^\circ C$
Single Pulse Avalanche Energy	$E_{AS}$	180	mJ
Avalanche Current	$I_{AS}$	60	A

**•Thermal resistance**

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	$R_{thJC}$	-	-	1	$^{\circ}C/W$
Thermal resistance, junction - ambient	$R_{thJA}$	-	-	25	$^{\circ}C/W$
Soldering temperature, wavesoldering for 10s	$T_{sold}$	-	-	265	$^{\circ}C$

**•Electronic Characteristics**

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS} = 0V, I_D = -250\mu A$	-30			V
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = -250\mu A$	-1.2		-2.5	V
Drain-Source Leakage Current	$I_{DSS}$	$V_{DS} = -30V, V_{GS} = 0V$			-1.0	$\mu A$
Gate- Source Leakage Current	$I_{GSS}$	$V_{GS} = \pm 20V, V_{DS} = 0V$			$\pm 100$	nA
Static Drain-source On Resistance	$R_{DS(ON)}$	$V_{GS} = -10V, I_D = -20A$		3.5	4.5	m $\Omega$
		$V_{GS} = -4.5V, I_D = -10A$		5	6	m $\Omega$
Forward Transconductance	$g_{FS}$	$V_{DS} = -10V, I_D = -5A$		20		S
Source-drain voltage	$V_{SD}$	$I_S = -20A$			1.28	V

**•Electronic Characteristics**

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Input capacitance	$C_{iss}$	f = 1MHz	-	4500	-	pF
Output capacitance	$C_{oss}$		-	398	-	
Reverse transfer capacitance	$C_{rss}$		-	157	-	

**•Gate Charge characteristics( $T_a = 25^{\circ}C$ )**

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Total gate charge	$Q_g$	$V_{DD} = -15V$	-	84	-	nC
Gate - Source charge	$Q_{gs}$	$I_D = -20A$	-	20	-	
Gate - Drain charge	$Q_{gd}$	$V_{GS} = -10V$	-	9.7	-	

Note: ① Pulse Test : Pulse width  $\leq 300\mu s$ , Duty cycle  $\leq 2\%$  ;

② Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate;

Fig.1 Gate-Charge Characteristics

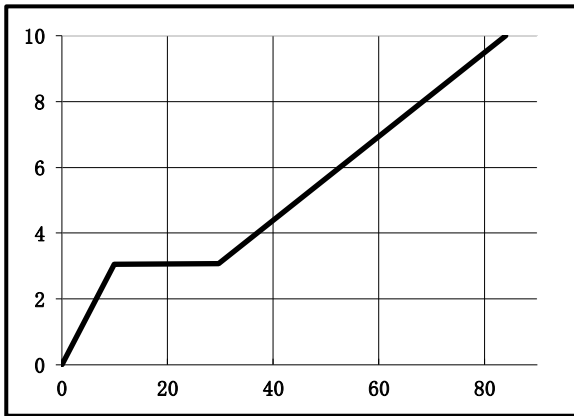


Fig.2 Capacitance Characteristics

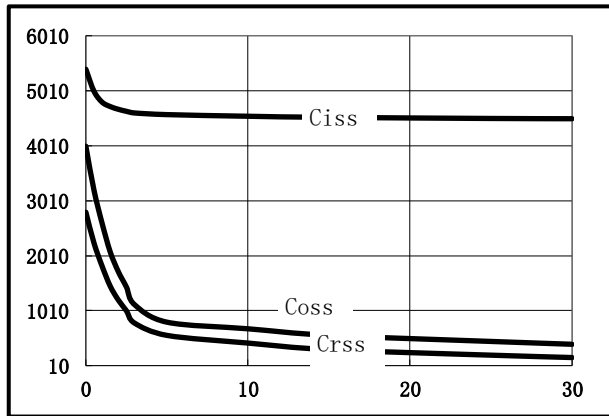


Fig.3 Power Dissipation

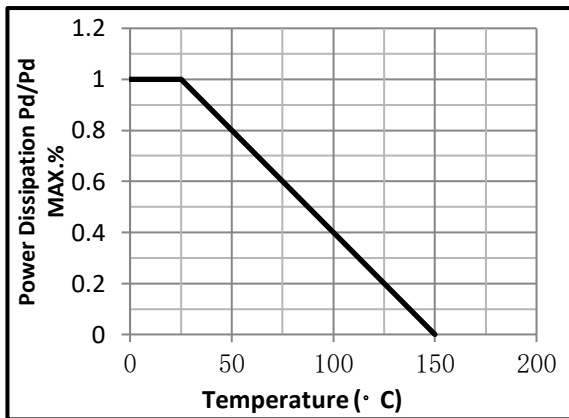


Fig.4 Typical output Characteristics

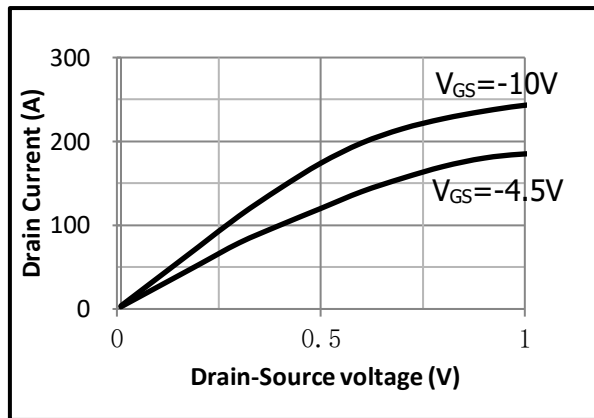


Fig.5 Threshold Voltage V.S Junction Temperature

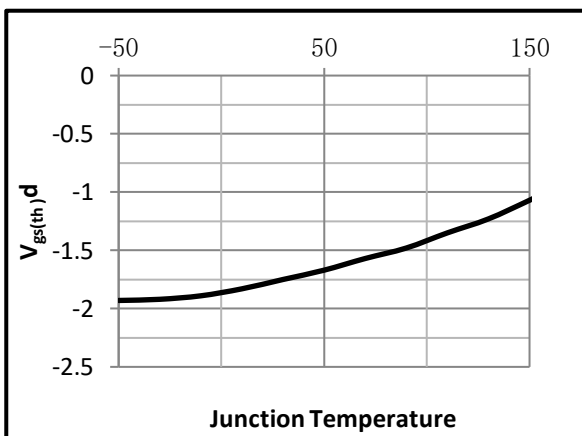


Fig.6 Resistance V.S Drain Current

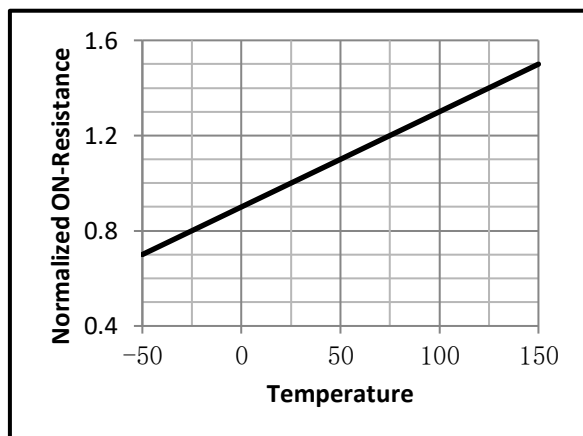


Fig.7 On-Resistance VS Gate Source Voltage

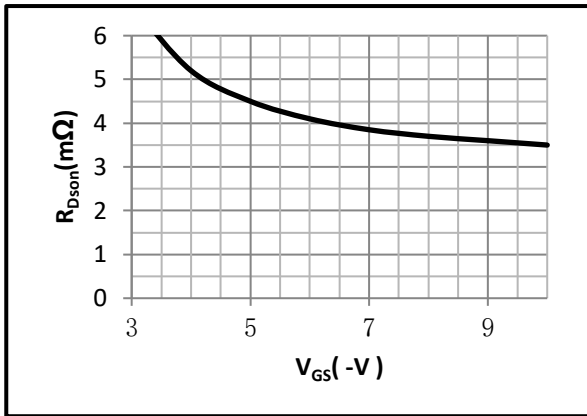


Fig.8 On-Resistance V.S Junction Temperature

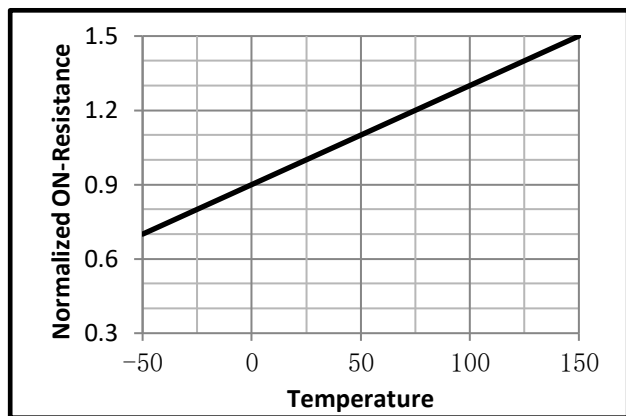


Fig.9 Switching Time Measurement Circuit

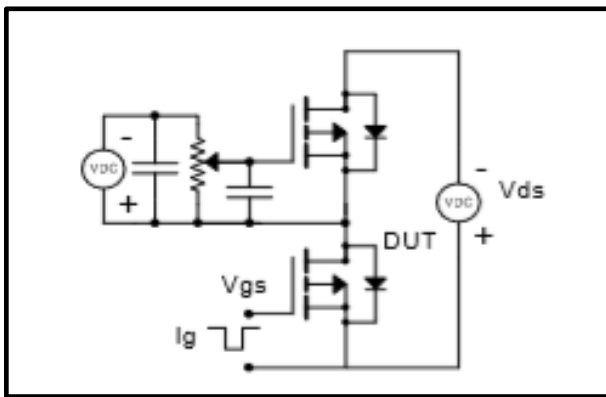


Fig.10 Gate Charge Waveform

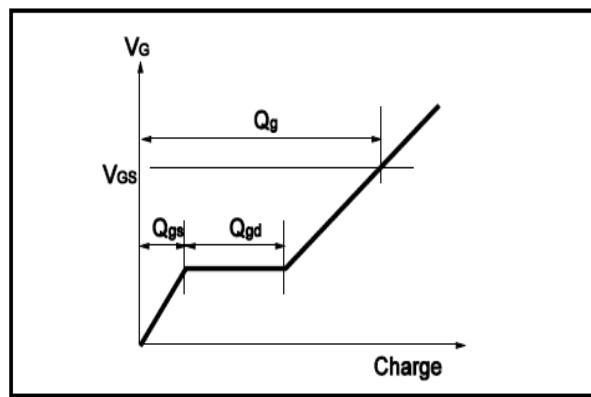


Fig.11 Switching Time Measurement Circuit

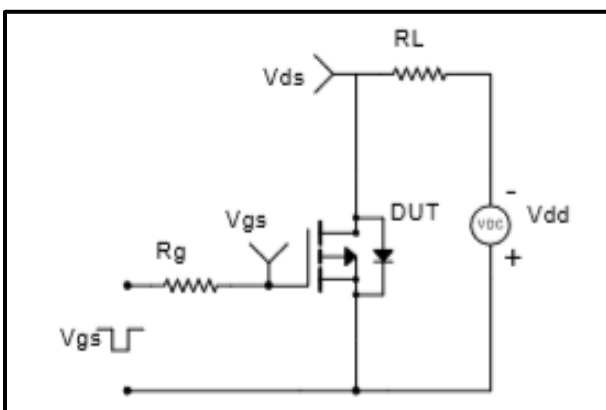
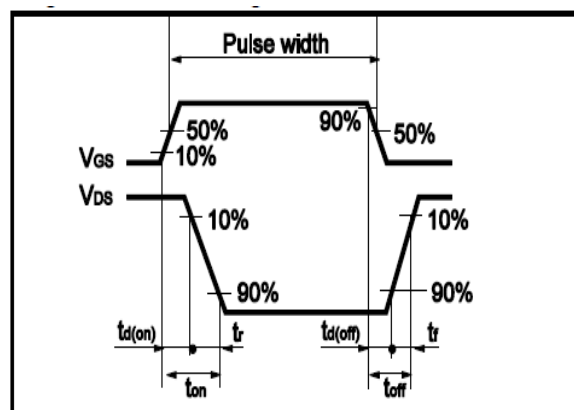


Fig.12 Gate Charge Waveform





•Dimensions (TO-263)

Unit: mm

SYMBOL	min	max	SYMBOL	min	max
A	2.10	2.50	B	0.85	1.25
b	0.50	0.80	b1	0.50	0.90
b2	0.45	0.70	C	0.45	0.70
D	6.30	6.75	D1	5.10	5.50
E	5.30	6.30	e1	2.25	2.35
L1	9.20	10.60	e2	4.45	4.75
L2	0.90	1.75	L3	0.60	1.10
K	0.00	0.23			

